



<b>[WE2] Nano Devices Using 2D Materials II</b>	
<b>Date / Time</b>	July 25 (Wed.), 2018 / 13:20-15:00
<b>Place</b>	Room E (#107~108)
<b>Session Chair(s)</b>	Won Jong Yoo (Sungkyunkwan Univ., Korea)

**WE2-1 [Invited]**

**13:20-13:50**

**2D Materials Based ISFETs for pH Sensing Applications**

Chunxiang Zhu

*Nat'l Univ. of Singapore, Singapore*

**WE2-2 [Invited]**

**13:50-14:20**

**Energy Dissipation and Light Emission in Graphene**

Myung-Ho Bae

*KRISS, Korea*

**WE2-3**

**14:20-14:40**

**Top-Gated MoS<sub>2</sub> Field-Effect Transistor with Ultra-Thin HfO<sub>2</sub> Gate Dielectric Formed by Hf-Seeded Atomic Layer Deposition**

Hojoon Kim<sup>1</sup>, Taejin Park<sup>1</sup>, Seongjae Park<sup>1</sup>, Mirine Leem<sup>1</sup>, Wonsik Ahn<sup>1</sup>, Seong-Jun Jeong<sup>2</sup>, Seongjun Park<sup>2</sup>, Yunseok Kim<sup>1</sup>, and Hyongsub Kim<sup>1</sup>

<sup>1</sup>*Sungkyunkwan Univ., Korea*, <sup>2</sup>*Samsung Advanced Inst. of Tech., Korea*

**WE2-4**

**14:40-15:00**

**Characterization of Defects in 2D Materials with Tip Enhanced Raman Scattering**

Byeong Geun Jeong<sup>1</sup>, Chanwoo Lee<sup>1</sup>, Seung Mi Lee<sup>2</sup>, and Mun Seok Jeong<sup>1</sup>

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